



## DMN6040SFDEQ

### **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> MAX	I <sub>D MAX</sub> T <sub>A</sub> = +25°C
60V	38mΩ @ V <sub>GS</sub> = 10V	6.5A
000	47mΩ @ V <sub>GS</sub> = 4.5V	5.2A

# **Description and Applications**

This MOSFET is designed to meet the stringent requirements of Automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- Power Management Functions
- DC-DC Converters
- Backlighting

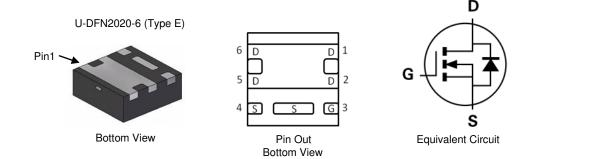
### 60V N-CHANNEL ENHANCEMENT MODE MOSFET

## **Features and Benefits**

- 100% Unclamped Inductive Switch (UIS) Test in Production
- 0.6mm Profile Ideal for Low Profile Applications
- PCB Footprint of 4mm<sup>2</sup>
- Low On-Resistance
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

## **Mechanical Data**

- Case: U-DFN2020-6 (Type E)
- Case Material: Molded Plastic, "Green" Molding Compound.
   UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @4
- Weight: 0.0065 grams (Approximate)



## Ordering Information (Note 5)

Part Number	Case	Packaging
DMN6040SFDEQ-7	U-DFN2020-6 (Type E)	3,000 / Tape & Reel
DMN6040SFDEQ-13	U-DFN2020-6 (Type E)	10,000 / Tape & Reel

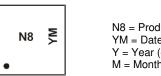
Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. 2. See http://www.diodes.com/quality/lead\_free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <100ppm antimony compounds.

4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to https://www.diodes.com/quality/.

5. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

# **Marking Information**



N8 = Product Type Marking Code

- YM = Date Code Marking
- Y = Year (ex: F = 2018)

M = Month (ex: 9 = September)

#### Date Code Key

Year	201	8	2019		2020	20	21	2022		2023	2	2024
Code	F		G		Н			J		К		L
Month	Jan	Feb	Mar	Apr	Мау	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



# **Maximum Ratings** (@ $T_A = +25^{\circ}C$ , unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage		V <sub>DSS</sub>	60	V	
Gate-Source Voltage			V <sub>GSS</sub>	±20	V
	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	ID	5.3 4.1	А
Continuous Drain Current (Note 7) $V_{GS} = 10V$	t<10s	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	ID	6.5 5.1	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%		I <sub>DM</sub>	30	А	
Maximum Body Diode Continuous Current		Is	2.5	А	
Avalanche Current (Note 8) L = 0.1mH	I <sub>AR</sub>	14.2	А		
Avalanche Energy (Note 8) L = 0.1mH	E <sub>AR</sub>	10	mJ		

# **Thermal Characteristics**

Characteristic		Symbol	Value	Unit	
Total Bower Dissinction (Note 6)	T <sub>A</sub> = +25°C	Р	0.66	W	
Total Power Dissipation (Note 6)	$T_A = +70^{\circ}C$	PD	0.42	vv	
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	Р	189	°C/W	
Thermal Resistance, Junction to Ambient (Note 0)	t<10s	$R_{ heta JA}$	132	C/W	
Total Power Dissipation (Note 7)	T <sub>A</sub> = +25°C	Р	2.03	W	
Total Fower Dissipation (Note 7)	$T_A = +70^{\circ}C$	PD	1.31	vv	
Thermal Resistance. Junction to Ambient (Note 7)	Steady State	Р	61		
memai resistance, sunction to Ambient (Note 7)	t<10s	$R_{ extsf{ heta}JA}$	43	°C/W	
Thermal Resistance, Junction to Case (Note 7)		$R_{\theta JC}$	9.3		
Operating and Storage Temperature Range		TJ. TSTG	-55 to +150	°C	

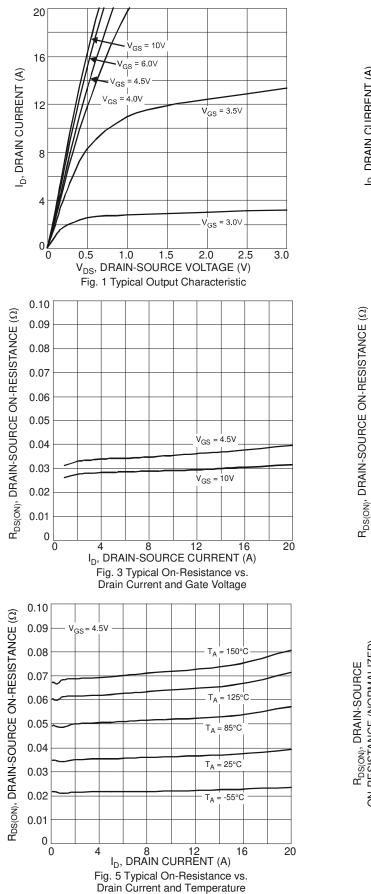
# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

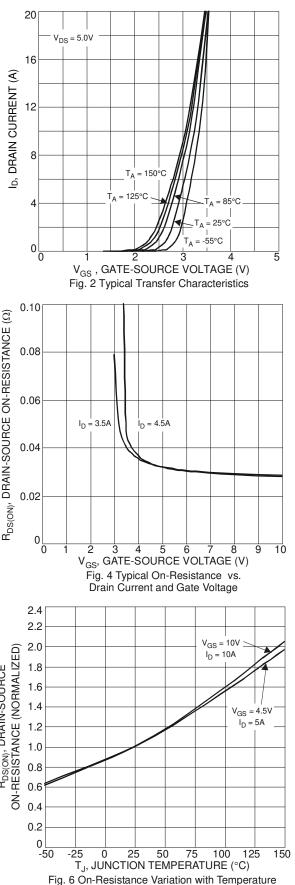
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 9)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	60	_	_	V	$V_{GS} = 0V, I_D = 250 \mu A$	
Zero Gate Voltage Drain Current	IDSS	_	_	100	nA	$V_{DS} = 60V, V_{GS} = 0V$	
Gate-Source Leakage	IGSS	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 9)							
Gate Threshold Voltage	V <sub>GS(TH)</sub>	1	—	3	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$	
Static Drain-Source On-Resistance	_	_	30	38	mΩ	$V_{GS} = 10V, I_D = 4.3A$	
Static Dialit-Source Off-Hesistance	R <sub>DS(ON)</sub>		35	47	1115.2	$V_{GS}=4.5V,\ I_D=4A$	
Forward Transfer Admittance	Y <sub>fs</sub>	_	4.5	_	S	$V_{DS} = 10V, I_D = 4.3A$	
Diode Forward Voltage	V <sub>SD</sub>	_	0.7	1.2	V	$V_{GS} = 0V, I_{S} = 1A$	
DYNAMIC CHARACTERISTICS (Note 10)							
Input Capacitance	C <sub>iss</sub>	_	1287	_		$V_{DS} = 25V, V_{GS} = 0V$ f = 1.0MHz	
Output Capacitance	Coss		57		pF		
Reverse Transfer Capacitance	C <sub>rss</sub>	_	44	_		1 = 1.00012	
Gate Resistance	R <sub>g</sub>		1.2	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$	
Total Gate Charge (V <sub>GS</sub> = 10V)	Qg	_	22.4	_			
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Qg		10.4		nC	$V_{DS} = 30V. I_{D} = 4.3A$	
Gate-Source Charge	Q <sub>gs</sub>		4.9		10	$v_{\rm DS} = 30 v, i_{\rm D} = 4.3 A$	
Gate-Drain Charge	Q <sub>gd</sub>	_	3.0	_			
Turn-On Delay Time	t <sub>D(ON)</sub>	_	6.6	_			
Turn-On Rise Time	t <sub>R</sub>	_	8.1	_	ns	$V_{GS} = 10V, V_{DD} = 30V, R_g = 6\Omega,$	
Turn-Off Delay Time	t <sub>D(OFF)</sub>		20.1		115	I <sub>D</sub> = 4.3A	
Turn-Off Fall Time	tF	_	4.0	_			
Body Diode Reverse Recovery Time	t <sub>RR</sub>	_	18	_	ns	$I_{S} = 4.3A$ , $dI/dt = 100A/\mu s$	
Body Diode Reverse Recovery Charge	Q <sub>RR</sub>		11.9		nC	I <sub>S</sub> = 4.3A, dl/dt = 100A/µs	

6. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
7. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
8. I<sub>AR</sub> and E<sub>AR</sub> ratings are based on low frequency and duty cycles to keep T<sub>J</sub> = +25°C.
9. Short duration pulse test used to minimize self-heating effect.
10. Guaranteed by design. Not subject to product testing. Notes:



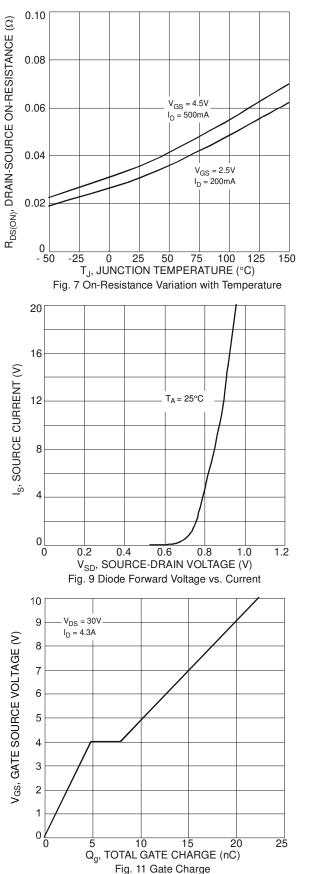


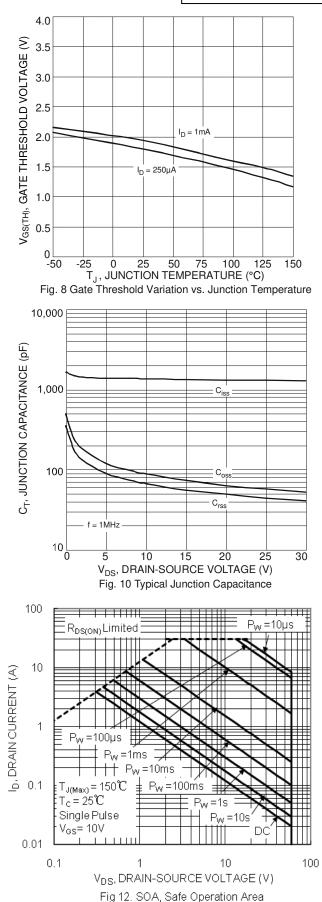




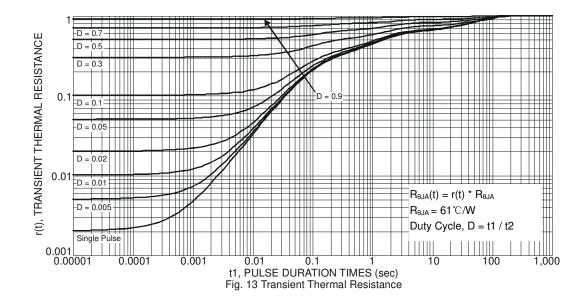










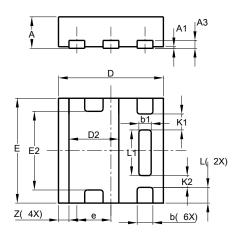




## **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

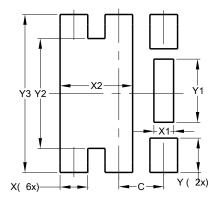
U-DFN2020-6 (Type E)



U-DFN2020-6							
(Туре Е)							
Dim	Min	Max	Тур				
Α	0.57	0.63	0.60				
A1	0	0.05	0.03				
A3	-	-	0.15				
b	0.2	0.35	0.30				
b1	0.185	0.285	0.235				
D	1.95	2.05	2.00				
D2	0.85	1.05	0.95				
Е	1.95	2.05	2.00				
E2	1.40	1.60	1.50				
е	-	-	0.65				
L	0.25	0.35	0.30				
L1	0.82	0.92	0.87				
K1	_	_	0.305				
K2	_	_	0.225				
Z	-	-	0.20				
All	All Dimensions in mm						

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.



U-DFN2020-6 (Type E)

Dimensions	Value			
Dimensions	(in mm)			
С	0.650			
Х	0.400			
X1	0.285			
X2	1.050			
Y	0.500			
Y1	0.920			
Y2	1.600			
Y3	2.300			

### DMN6040SFDEQ Datasheet number: DS41178 Rev. 1 - 2



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